Maximum Ratings N-CHANNEL – Q1 (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Units
Drain-Source Voltage			V_{DSS}	60	V
Gate-Source Voltage			V_{GSS}	±20	V
Continuous Drain Current (Note 7) V_{GS} = 10V	Steady State	T_A = +25°C T_A = +70°C	I_D	500 400	mA
	t<10s	T_A = +25°C T_A = +70°C	I_D	620 480	mA
Pulsed Drain Current (Note 7)			I_{DM}	1000	mA

Maximum Ratings P-CHANNEL – Q2 (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Units
Drain-Source Voltage			V_{DSS}	-60	V
Gate-Source Voltage			V_{GSS}	±20	V
Continuous Drain Current (Note 7) V_{GS} = -10V	Steady State	T_A = +25°C T_A = +70°C	I_D	-360 -280	mA
	t<10s	T_A = +25°C T_A = +70°C	I_D	-410 -320	mA
Pulsed Drain Current (Note 7)			I_{DM}	-650	mA

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Units
Total Power Dissipation (Note 6)	T_A = +25°C	P_D	0.45	W
	T_A = +70°C		0.28	
Thermal Resistance, Junction to Ambient (Note 6)	Steady state	$R_{\theta JA}$	281	°C/W
	t<10s		210	
Total Power Dissipation (Note 7)	T_A = +25°C	P_D	1	W
	T_A = +70°C		0.62	
Thermal Resistance, Junction to Ambient (Note 7)	Steady state	$R_{\theta JA}$	129	°C/W
	t<10s		97	
Operating and Storage Temperature Range		T_J, T_{STG}	-55 to +150	°C

Notes: 6. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
7. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.

Electrical Characteristics N-CHANNEL – Q1 (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						
Drain-Source Breakdown Voltage	BV_{DSS}	60	—	—	V	V_{GS} = 0V, I_D = 250μA
Zero Gate Voltage Drain Current @T_C = +25°C	I_{DSS}	—	—	10	nA	V_{DS} =50V, V_{GS} = 0V
Gate-Source Leakage	I_{GSS}	—	—	±50	nA	V_{GS} = ±5V, V_{DS} = 0V
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	$V_{GS(th)}$	1.0	—	2.5	V	V_{DS} = V_{GS}, I_D = 250μA
Static Drain-Source On-Resistance	$R_{DS(ON)}$	—	1.3	1.7	Ω	V_{GS} = 10V, I_D = 500mA
		—	1.5	3		V_{GS} = 4.5V, I_D = 200mA
Forward Transfer Admittance	$\|Y_{fs}\|$	80	—	—	mS	V_{DS} = 10V, I_D = 200mA
Diode Forward Voltage	V_{SD}	—	—	1.4	V	V_{GS} = 0V, I_S = 115mA
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	C_{iss}	—	30	—	pF	V_{DS} = 25V, V_{GS} = 0V, f = 1.0MHz
Output Capacitance	C_{oss}	—	4.2	—	pF	
Reverse Transfer Capacitance	C_{rss}	—	2.9	—	pF	
Total Gate Charge	Q_g	—	0.3	—	nC	V_{GS} = 4.5V, V_{DS} = 10V, I_D = 250mA
Gate-Source Charge	Q_{gs}	—	0.2	—	nC	
Gate-Drain Charge	Q_{gd}	—	0.08	—	nC	
Turn-On Delay Time	$t_{D(on)}$	—	3.9	—	ns	V_{DD} = 30V, V_{GS} = 10V, R_G = 25Ω, I_D = 200mA
Turn-On Rise Time	t_r	—	3.4	—	ns	
Turn-Off Delay Time	$t_{D(off)}$	—	15.7	—	ns	
Turn-Off Fall Time	t_f	—	9.9	—	ns	

Electrical Characteristics P-CHANNEL – Q2 (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						
Drain-Source Breakdown Voltage	BV_{DSS}	-60	—	—	V	V_{GS} = 0V, I_D = -250μA
Zero Gate Voltage Drain Current @T_C = +25°C	I_{DSS}	—	—	-25	nA	V_{DS} = -50V, V_{GS} = 0V
Gate-Source Leakage	I_{GSS}	—	—	±100	nA	V_{GS} = ±5V, V_{DS} = 0V
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	$V_{GS(th)}$	-1	—	-3.0	V	V_{DS} = V_{GS}, I_D = -250μA
Static Drain-Source On-Resistance	$R_{DS\ (ON)}$	—	2.7	4	Ω	V_{GS} = -10V, I_D = -500mA
		—	3.2	6		V_{GS} = -4.5V, I_D = -200mA
Forward Transfer Admittance	$\|Y_{fs}\|$	50	—	—	mS	V_{DS} = -25V, I_D = -100mA
Diode Forward Voltage	V_{SD}	—	—	-1.4	V	V_{GS} = 0V, I_S = -115mA
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	C_{iss}	—	25	—	pF	V_{DS} = -25V, V_{GS} = 0V, f = 1.0MHz
Output Capacitance	C_{oss}	—	4.7	—	pF	
Reverse Transfer Capacitance	C_{rss}	—	2.7	—	pF	
Total Gate Charge	Q_g	—	0.28	—	nC	V_{GS} = -4.5V, V_{DS} = -10V, I_D = -500mA
Gate-Source Charge	Q_{gs}	—	0.14	—	nC	
Gate-Drain Charge	Q_{gd}	—	0.08	—	nC	
Turn-On Delay Time	$t_{D(on)}$	—	5.5	—	ns	V_{DD} = -30V, V_{GS} = -10V, R_G = 50Ω, I_D = -270mA
Turn-On Rise Time	t_r	—	7.9	—	ns	
Turn-Off Delay Time	$t_{D(off)}$	—	10.6	—	ns	
Turn-Off Fall Time	t_f	—	11.6	—	ns	

Notes: 8. Short duration pulse test used to minimize self-heating effect.
9. Guaranteed by design. Not subject to product testing.

N-CHANNEL – Q1

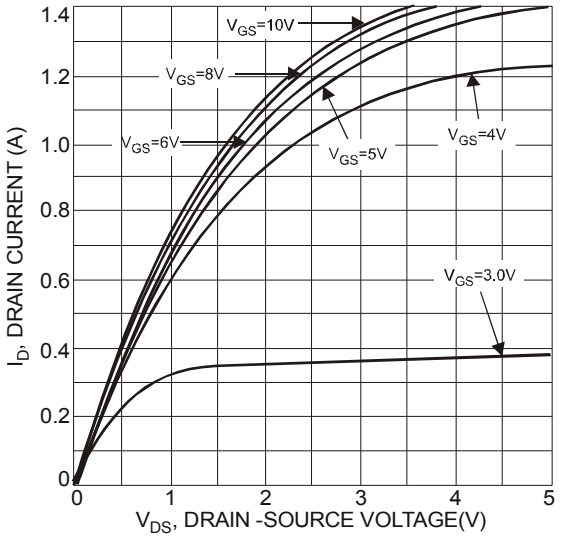


Fig. 1 Typical Output Characteristics

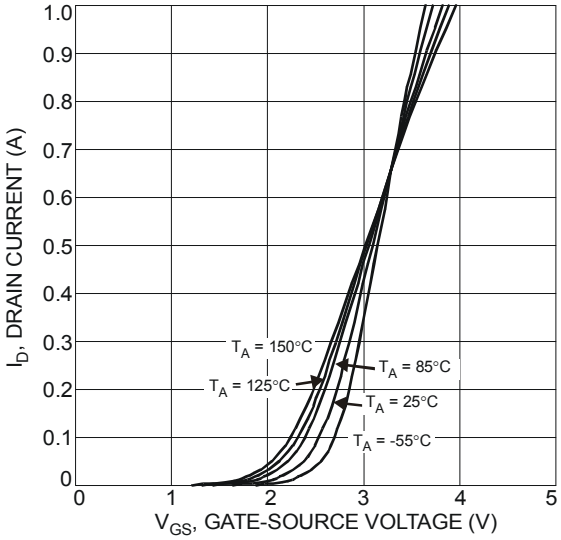


Fig. 2 Typical Transfer Characteristics

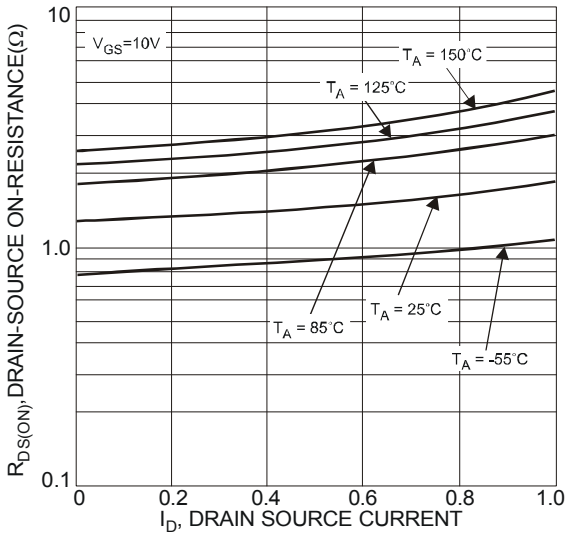


Fig. 3 Typical On-Resistance vs. Drain Current and Gate Voltage

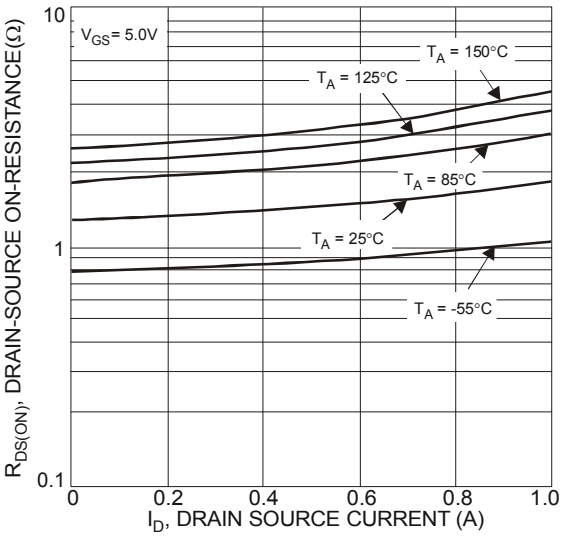


Fig. 4 Typical On-Resistance vs. Drain Current and Temperature

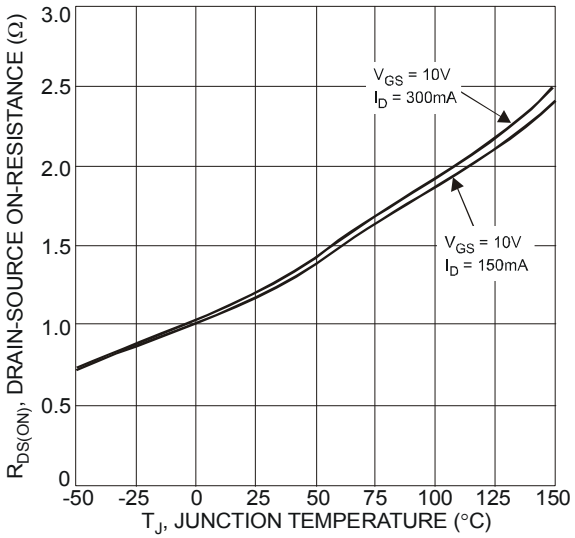


Fig. 5 On-Resistance Variation with Temperature

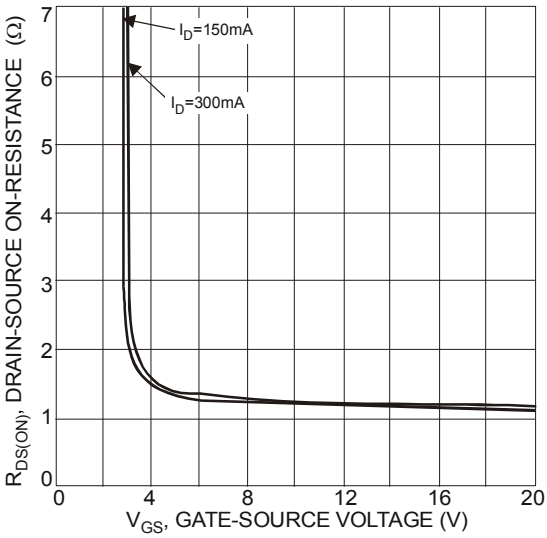


Fig. 6 Static Drain-Source On-Resistance vs. Gate-Source Voltage

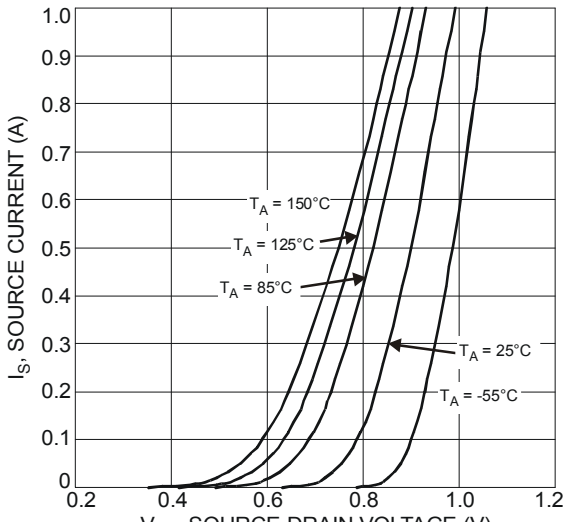


Fig. 7 Diode Forward Voltage vs. Current

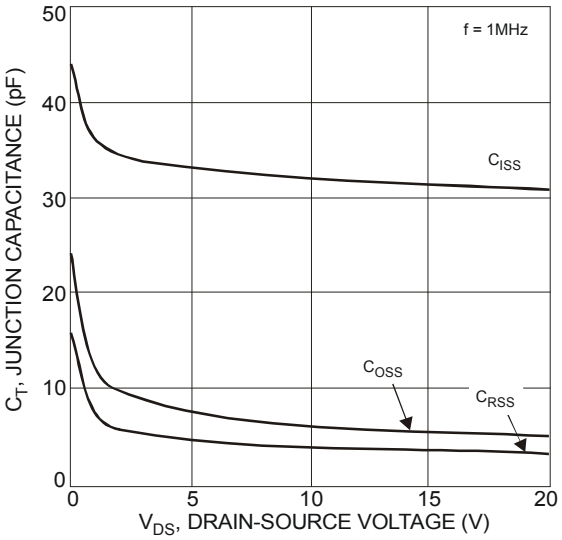


Fig. 8 Typical Junction Capacitance

P-CHANNEL – Q2

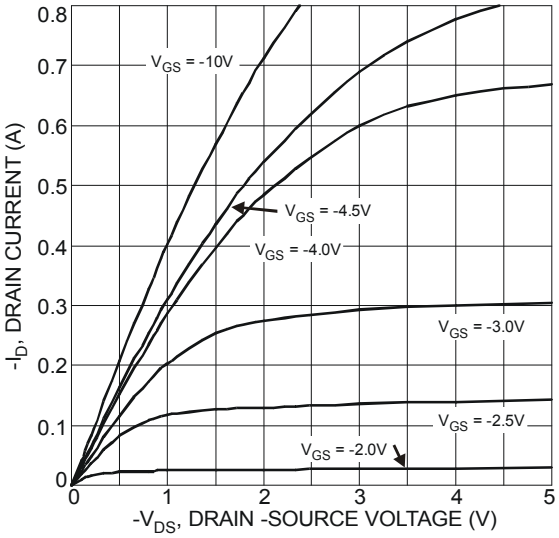


Fig. 9 Typical Output Characteristics

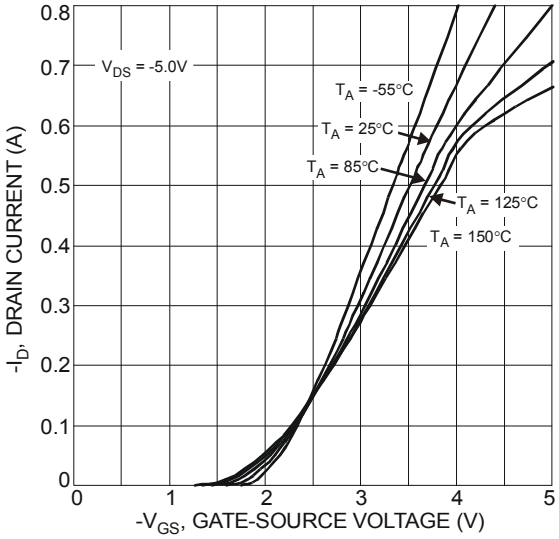


Fig. 10 Typical Transfer Characteristics

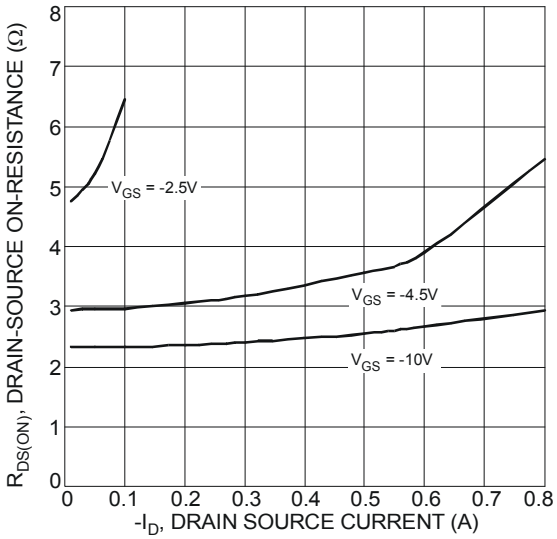


Fig. 11 Typical On-Resistance vs. Drain Current and Gate Voltage

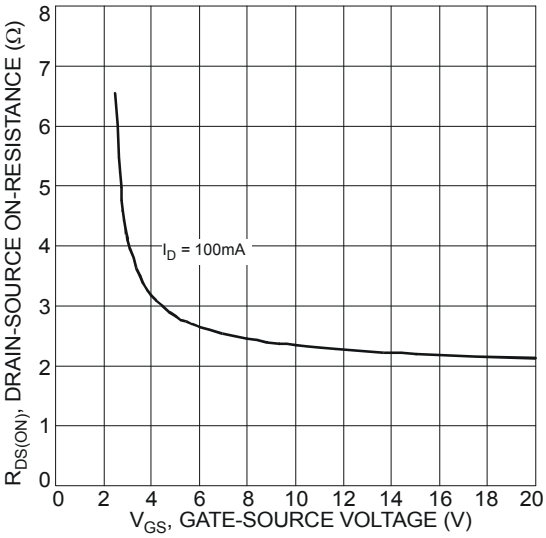


Fig. 12 Typical Drain-Source On-Resistance vs. Gate-Source Voltage

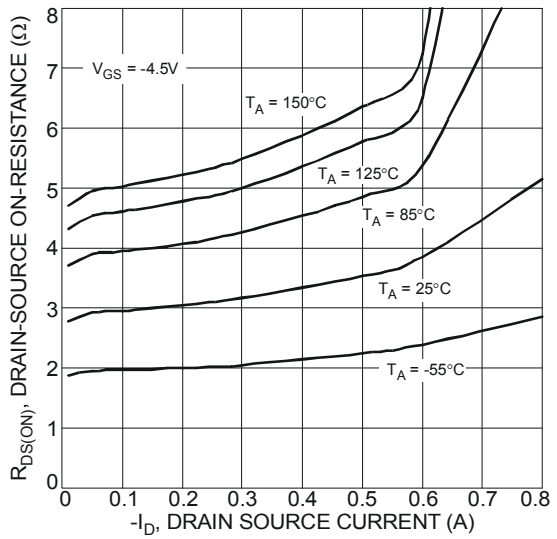


Fig. 13 Typical On-Resistance vs. Drain Current and Temperature

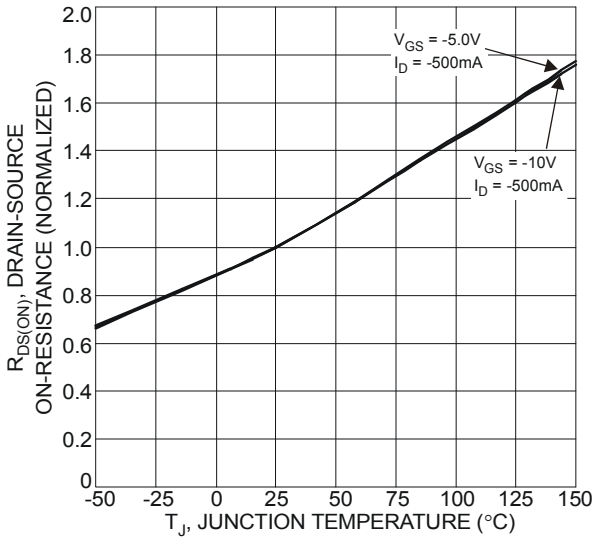


Fig. 14 On-Resistance Variation with Temperature

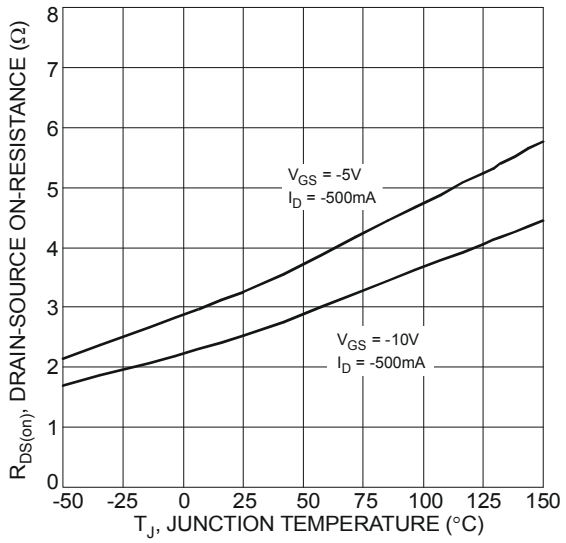


Fig. 15 On-Resistance Variation with Temperature

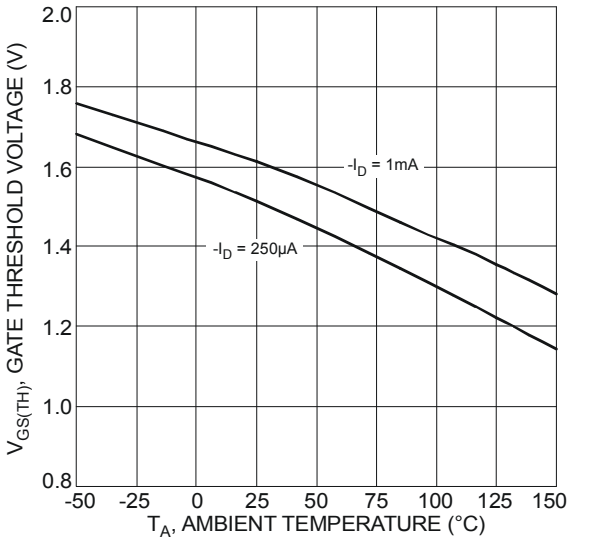


Fig. 16 Gate Threshold Variation vs. Ambient Temperature

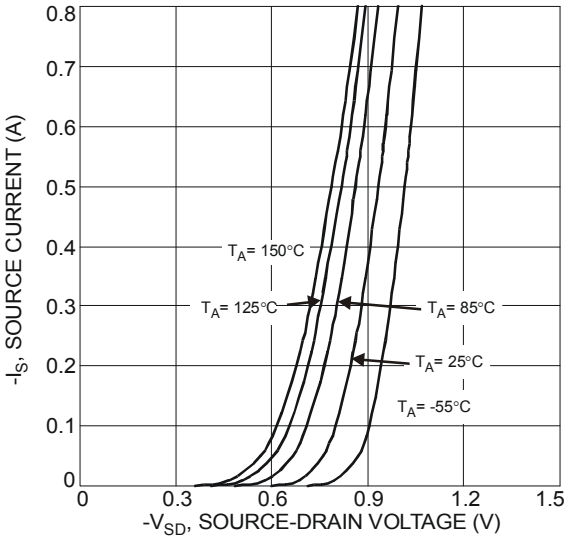


Fig. 17 Diode Forward Voltage vs. Current

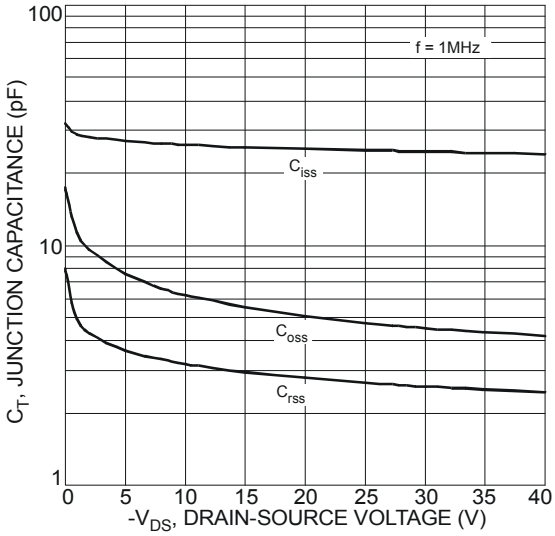


Fig. 18 Typical Junction Capacitance

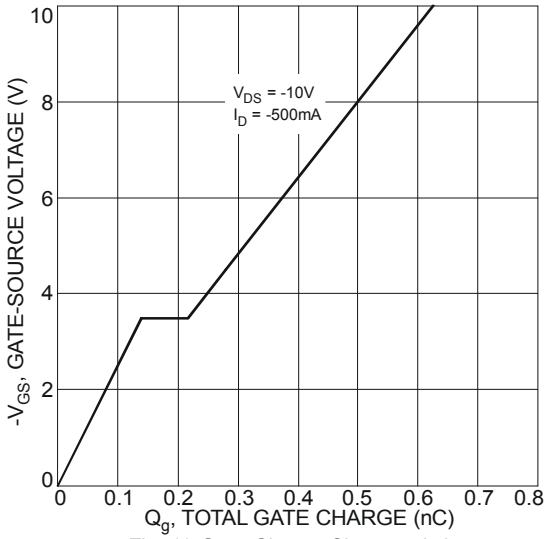
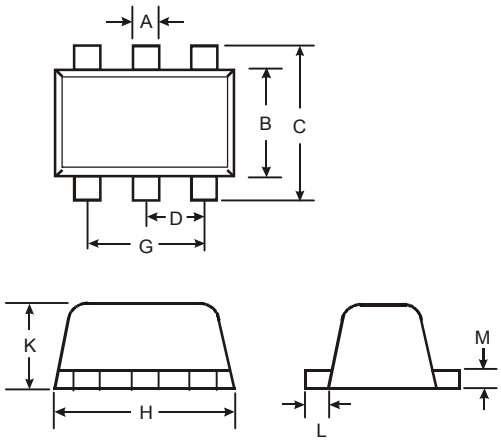


Fig. 19 Gate-Charge Characteristics

Package Outline Dimensions

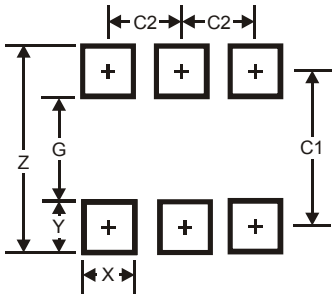
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



SOT563			
Dim	**Min**	**Max**	**Typ**
A	0.15	0.30	0.20
B	1.10	1.25	1.20
C	1.55	1.70	1.60
D	-	-	0.50
G	0.90	1.10	1.00
H	1.50	1.70	1.60
K	0.55	0.60	0.60
L	0.10	0.30	0.20
M	0.10	0.18	0.11
All Dimensions in mm			

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for latest version.



Dimensions	Value (in mm)
Z	2.2
G	1.2
X	0.375
Y	0.5
C1	1.7
C2	0.5

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